Europäisches Patentamt
European Patent Office
Office européen des brevets

(II) Publication number:

0 **356 059** A3

(12)

EUROPEAN PATENT APPLICATION

- (1) Application number: 89308007.7
- ① Int. CI.4 H01L 21/38 , H01L 21/477 , H01L 33/00

- ② Date of filing: 07.08.89
- Priority: 15.08.88 US 232405 22.08.88 US 234802
- ① Date of publication of application: 28,02.90 Bulletin 90/09
- Designated Contracting States:
 DE FR GB NL
- Date of deterred publication of the search report: 02.05.90 Buffetin 90/18
- Applicant: Neumark, Gertrude F. 153 Old Colony Road Hartsdale New York 10530(US)
- Inventor: Neumark, Gertrude F. 153 Old Colony Road Hartsdale New York 10530(US)
- Representative: Aliem, Peter Clerk et al LLOYD WISE, TREGEAR & CO. Norman House 105-109 Strand London WC2R 0AE(GB)
- Process for doping crystals of wide band gap semiconductors.
- (f) Non-equilibrium impurity incorporation is used to dope hard-to-dope crystais of wide band gap semi-conductors, such as zinc selenide and zinc telluride. This involves incorporating into the crystal a compensating pair of primary and secondary dopants, thereby to increase the solubility of either dopant alone in the crystal. Thereafter, the secondary more mobile dopant is removed preferentially, leaving the primary dopant predominant. This technique is used to dope zinc selenide p-type by the use of nitrogen as the primary dopant and lithium as the secondary dopant. Alternatively, the technique may use nitrogen as the primary dopant and the hydrogen as the secondary dopant to obtain low resistivity p-type zinc selenide.

EP 0 356 059 A3

Xerox Copy Centre



EUROPEAN SEARCH REPORT

EP 89 30 8007

Category	Citation of document with of relevant p	indication, where appropriate,	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. CL 5)					
A	SEMICONDUCTOR SCIEI vol. 2, no. 10, Oct 629-635, IOP Public GB; F. EL. AKKAD: ' phosphorus impuritat * Page 632, right-i paragraphs 3-4 *	tober 1987, pages shing Ltd, Bristol, 'Lithium and les in ZnTe"	1,4,5,7	H 01 L 21/38 H 01 L 21/477 H 01 L 33/00					
A	JOURNAL OF APPLIED no. 7, June 1971, 17 TELL: "Properties of CdS" * Page 2922, right-paragraph - page 29 column, paragraph 1	pages 2919-2924; B. of the alkalis in -hand column, last 923, left-hand	1						
	no. 1, February 197 Plenum Publishing.0	Corp., New York, US; Some characteristics Shigh conductivity and ZnSxSe1-x	1,7	TECHNICAL FIELDS SEARCHED (int. Cl.3)					
	PATENT ABSTRACTS OF 423 (E-680), 9th No JP-A-63 160 344 (TO 04-07-1988 * Abstract *		1,7						
-	APPLIED PHYSICS LET 1, 4th January 1988 American Institute YASUDA et al.: "Met phase epitaxy of lo ZnSe" * Abstract *	, pages 57-59, of Physics; T.	1,8,7						
	The precent search report has b	een drawn up for all claims	11	Bossum					
THE	Place of metric HAGUE	02-02-1990	GORI						
X : part	CATEGORY OF CITED DOCUME icularly relevant if taken sione lealarly relevant if combined with an iment of the same category aslogical background -written disclosure	E : earlier parent é after the filing other D : document cité L : document cité	T: theory or principle underlying the invention E: earlier patent document, but published on, or after the filing date D: document cited in the application L: document cited for other reasons 4: member of the spano patent family, corresponding						

O : non-written disclosure
P: latermediate document

& : member of the same pat document

Page

2

European Patent Office

EUROPEAN SEARCH REPORT

Application Number

EP 89 30 8007

	Citation of document with ind	ERED TO BE RELEVA	Rolevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl.5)				
P, X	of relevant page FR-A-2 613 136 (INC) * Page 8, line 14	180	1,2					
				TECHNICAL FIELDS SEARCHED (lat CL5)				
	·							
-	The present search report has	been drawn up for all claims						
-	Place of search	Date of completion of the sea	rch Cr	Executeer ORI P.				
g 1	HE HAGUE	02-02-1990						
20 X:	CATEGORY OF CITED DOCUMI particularly relevant if taken alone particularly relevant if combined with a document of the same category technological background non-written disclosure	nother D: document	Ol (DG 28 Me berent :	atlas				

,oj I •ù	Say Ivilla		7					4.5	'गुन्, '						1.	<u>.</u>		77° 790		
								\$1	.*			*				·	**		1	
			ý.					n. (*)				***				. *	s Si B			e e
ti. ≨rr									The same of the sa	2.7								1.4	#44	
34 73	5.;																*	100	•	
																			•	
5				5 . ₆ 5.	. t								1							
	- 4		ope ²	,				٧.			•	e de la companya de l					4			
*	ija		e ger e George						e ·								71.	i.		
									-				5 May 1							
	÷.			i	. 1							via :								
16 160				·				4 j 4									100		Say.	
	*		٠	R					32			ja Carj					4. 1	<u>, </u>		
	¥1		. * .	ē	n W			i i	4											
	. 0	7 J.	3 4.									1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1							70 (
L.F.	·			We.	**	* .		ξ <u>ξ</u>						•.						
10 m					**************************************														. ". "	
2				·w.s		4		er i											K.y.	
tine.		Police		* 1.5	i Se di			•											4	
	* 150 28		a		1.74	1		*									1	-		
\$P [2		54										, A.	
		***	· - •		\$ 90 P												** **		12.	
		1	4					đ.												
Pi.			پي آنه		•			*,									149			
		9											* .						4	
										4										
															·					
e de la companya de l				·*· 1		.,													٠	
						**	*													
								5	•											
									n.											
				el di																
á.		1.	* · ·																	
7.4				\hat{A}^{\prime}																
· (†)																				
<i></i>																				
																1.				
ķ.,												*.								
1																				
Ty F																				
· 通常的 1000 1000 1000 1000 1000 1000 1000 10																				
3 .																				